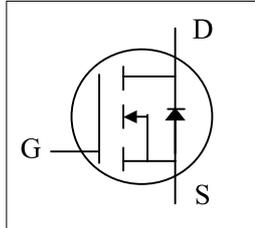




- ▼ Simple Drive Requirement
- ▼ Low Gate Charge
- ▼ Fast Switching Speed

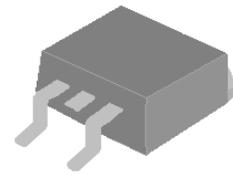


BV_{DSS}	30V
$R_{DS(ON)}$	12m Ω
I_D	45A

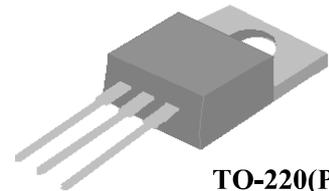
Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-263 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP60T03GP) are available for low-profile applications.



TO-263(S)



TO-220(P)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	45	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	32	A
I_{DM}	Pulsed Drain Current ¹	120	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	44	W
	Linear Derating Factor	0.352	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	3.4	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$